

## OptiMOS™ 2 Power-Transistor

### Features

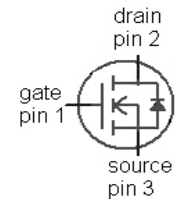
- N-channel, normal level
- Excellent gate charge x  $R_{DS(on)}$  product (FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target application
- Ideal for high-frequency switching and synchronous rectification
- Halogen-free according to IEC61249-2-21



### Product Summary

|                          |     |    |
|--------------------------|-----|----|
| $V_{DS}$                 | 85  | V  |
| $R_{DS(on),max}$ (TO263) | 8.2 | mΩ |
| $I_D$                    | 95  | A  |

| Type    | IPB08CNE8N G | IPI08CNE8N G | IPP08CNE8N G |
|---------|--------------|--------------|--------------|
|         |              |              |              |
| Package | PG-TO263-3   | PG-TO262-3   | PG-TO220-3   |
| Marking | 08CNE8N      | 08CNE8N      | 08CNE8N      |



Maximum ratings, at  $T_j=25\text{ °C}$ , unless otherwise specified

| Parameter                           | Symbol            | Conditions                                                                                           | Value       | Unit  |
|-------------------------------------|-------------------|------------------------------------------------------------------------------------------------------|-------------|-------|
| Continuous drain current            | $I_D$             | $T_C=25\text{ °C}$                                                                                   | 95          | A     |
|                                     |                   | $T_C=100\text{ °C}$                                                                                  | 68          |       |
| Pulsed drain current <sup>2)</sup>  | $I_{D,pulse}$     | $T_C=25\text{ °C}$                                                                                   | 380         |       |
| Avalanche energy, single pulse      | $E_{AS}$          | $I_D=95\text{ A}$ , $R_{GS}=25\text{ Ω}$                                                             | 262         | mJ    |
| Reverse diode $dv/dt$               | $dv/dt$           | $I_D=95\text{ A}$ , $V_{DS}=68\text{ V}$ ,<br>$di/dt=100\text{ A/μs}$ ,<br>$T_{j,max}=175\text{ °C}$ | 6           | kV/μs |
| Gate source voltage <sup>3)</sup>   | $V_{GS}$          |                                                                                                      | ±20         | V     |
| Power dissipation                   | $P_{tot}$         | $T_C=25\text{ °C}$                                                                                   | 167         | W     |
| Operating and storage temperature   | $T_j$ , $T_{stg}$ |                                                                                                      | -55 ... 175 | °C    |
| IEC climatic category; DIN IEC 68-1 |                   |                                                                                                      | 55/175/56   |       |

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Thermal characteristics

|                                                              |            |                                              |   |   |     |     |
|--------------------------------------------------------------|------------|----------------------------------------------|---|---|-----|-----|
| Thermal resistance, junction - case                          | $R_{thJC}$ |                                              | - | - | 0.9 | K/W |
| Thermal resistance, junction - ambient (TO220, TO262, TO263) | $R_{thJA}$ | minimal footprint                            | - | - | 62  |     |
|                                                              |            | 6 cm <sup>2</sup> cooling area <sup>4)</sup> | - | - | 40  |     |

#### Electrical characteristics, at $T_j=25\text{ °C}$ , unless otherwise specified

#### Static characteristics

|                                  |               |                                                              |    |     |     |               |
|----------------------------------|---------------|--------------------------------------------------------------|----|-----|-----|---------------|
| Drain-source breakdown voltage   | $V_{(BR)DSS}$ | $V_{GS}=0\text{ V}, I_D=1\text{ mA}$                         | 85 | -   | -   | V             |
| Gate threshold voltage           | $V_{GS(th)}$  | $V_{DS}=V_{GS}, I_D=130\text{ }\mu\text{A}$                  | 2  | 3   | 4   |               |
| Zero gate voltage drain current  | $I_{DSS}$     | $V_{DS}=68\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$    | -  | 0.1 | 1   | $\mu\text{A}$ |
|                                  |               | $V_{DS}=68\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}$   | -  | 10  | 100 |               |
| Gate-source leakage current      | $I_{GSS}$     | $V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$                      | -  | 1   | 100 | nA            |
| Drain-source on-state resistance | $R_{DS(on)}$  | $V_{GS}=10\text{ V}, I_D=95\text{ A}, (\text{TO263})$        | -  | 6.1 | 8.2 | m $\Omega$    |
|                                  |               | $V_{GS}=10\text{ V}, I_D=95\text{ A}, (\text{TO220, TO262})$ | -  | 6.4 |     |               |
| Gate resistance                  | $R_G$         |                                                              | -  | 1.5 | -   | $\Omega$      |
| Transconductance                 | $g_{fs}$      | $ V_{DS} >2 I_D R_{DS(on)max}, I_D=95\text{ A}$              | 57 | 113 | -   | S             |

<sup>1)</sup> J-STD20 and JESD22

<sup>2)</sup> See figure 3

<sup>3)</sup>  $T_{jmax}=150\text{ °C}$  and duty cycle  $D=0.01$  for  $V_{GS}<-5\text{ V}$

<sup>4)</sup> Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical in still air.

| Parameter | Symbol | Conditions | Values |      |      | Unit |
|-----------|--------|------------|--------|------|------|------|
|           |        |            | min.   | typ. | max. |      |

#### Dynamic characteristics

|                              |              |                                                                                   |   |      |      |    |
|------------------------------|--------------|-----------------------------------------------------------------------------------|---|------|------|----|
| Input capacitance            | $C_{iss}$    | $V_{GS}=0\text{ V}, V_{DS}=40\text{ V},$<br>$f=1\text{ MHz}$                      | - | 5030 | 6690 | pF |
| Output capacitance           | $C_{oss}$    |                                                                                   | - | 942  | 1250 |    |
| Reverse transfer capacitance | $C_{rss}$    |                                                                                   | - | 65   | 98   |    |
| Turn-on delay time           | $t_{d(on)}$  | $V_{DD}=40\text{ V}, V_{GS}=10\text{ V},$<br>$I_D=47.5\text{ A}, R_G=1.6\ \Omega$ | - | 15   | 23   | ns |
| Rise time                    | $t_r$        |                                                                                   | - | 24   | 36   |    |
| Turn-off delay time          | $t_{d(off)}$ |                                                                                   | - | 26   | 39   |    |
| Fall time                    | $t_f$        |                                                                                   | - | 6    | 10   |    |

#### Gate Charge Characteristics<sup>5)</sup>

|                       |               |                                                                            |   |     |    |    |
|-----------------------|---------------|----------------------------------------------------------------------------|---|-----|----|----|
| Gate to source charge | $Q_{gs}$      | $V_{DD}=40\text{ V}, I_D=95\text{ A},$<br>$V_{GS}=0\text{ to }10\text{ V}$ | - | 28  | 37 | nC |
| Gate to drain charge  | $Q_{gd}$      |                                                                            | - | 17  | 26 |    |
| Switching charge      | $Q_{sw}$      |                                                                            | - | 30  | 43 |    |
| Gate charge total     | $Q_g$         |                                                                            | - | 75  | 99 |    |
| Gate plateau voltage  | $V_{plateau}$ |                                                                            | - | 5.5 | -  | V  |
| Output charge         | $Q_{oss}$     | $V_{DD}=40\text{ V}, V_{GS}=0\text{ V}$                                    | - | 72  | 95 | nC |

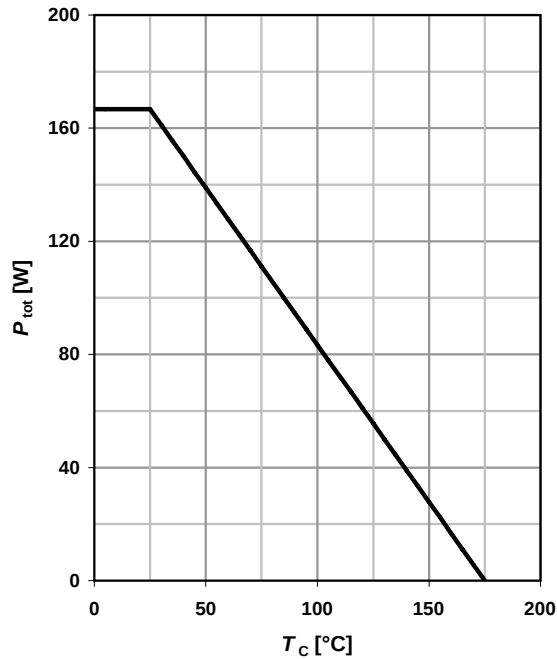
#### Reverse Diode

|                                  |               |                                                                   |   |     |     |    |
|----------------------------------|---------------|-------------------------------------------------------------------|---|-----|-----|----|
| Diode continuous forward current | $I_S$         | $T_C=25\text{ °C}$                                                | - | -   | 95  | A  |
| Diode pulse current              | $I_{S,pulse}$ |                                                                   | - | -   | 380 |    |
| Diode forward voltage            | $V_{SD}$      | $V_{GS}=0\text{ V}, I_F=95\text{ A},$<br>$T_j=25\text{ °C}$       | - | 1   | 1.2 | V  |
| Reverse recovery time            | $t_{rr}$      | $V_R=40\text{ V}, I_F=I_S,$<br>$di_F/dt=100\text{ A}/\mu\text{s}$ | - | 105 | -   | ns |
| Reverse recovery charge          | $Q_{rr}$      |                                                                   | - | 265 | -   | nC |

<sup>5)</sup> See figure 16 for gate charge parameter definition

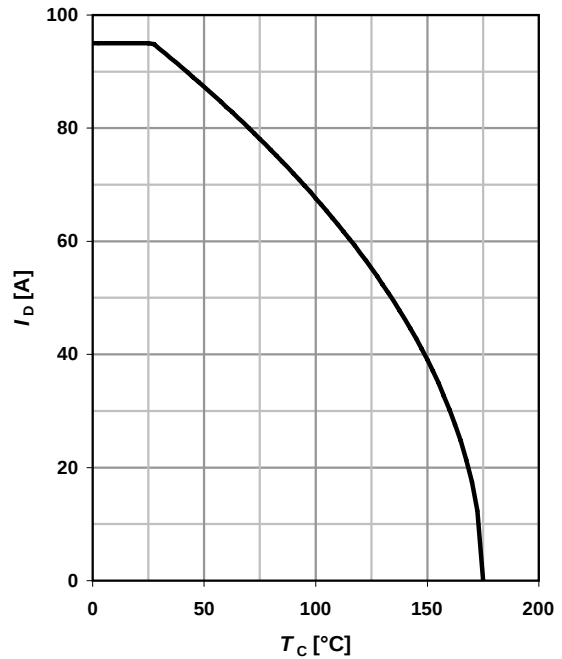
### 1 Power dissipation

$$P_{\text{tot}} = f(T_C)$$



### 2 Drain current

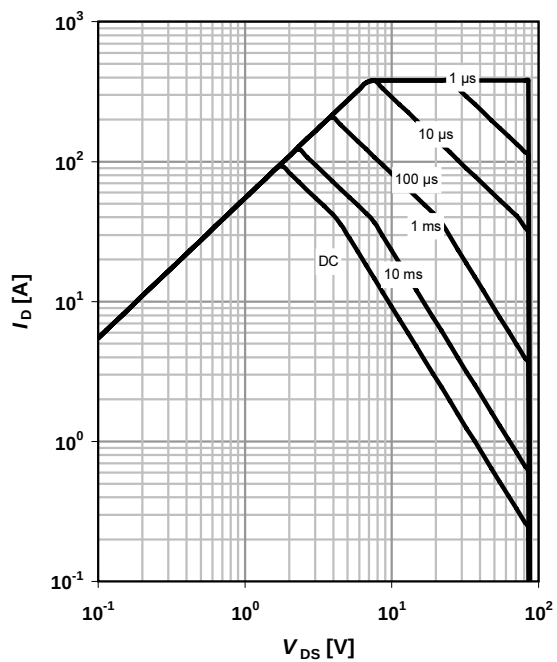
$$I_D = f(T_C); V_{GS} \geq 10 \text{ V}$$



### 3 Safe operating area

$$I_D = f(V_{DS}); T_C = 25 \text{ °C}; D = 0$$

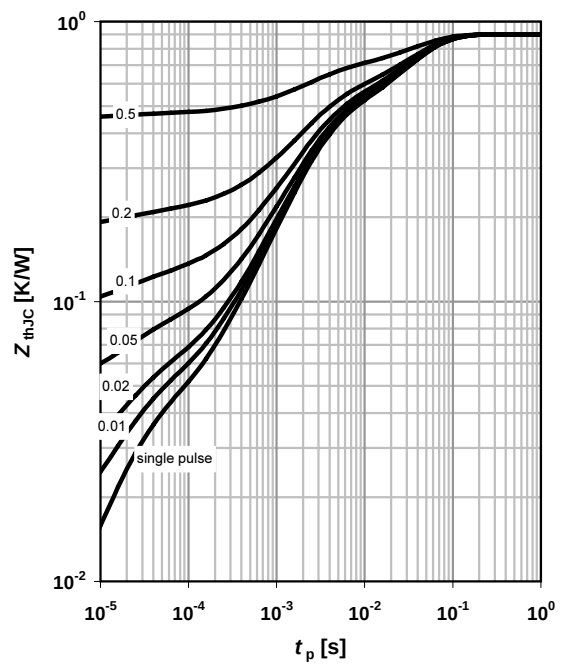
parameter:  $t_p$



### 4 Max. transient thermal impedance

$$Z_{\text{thJC}} = f(t_p)$$

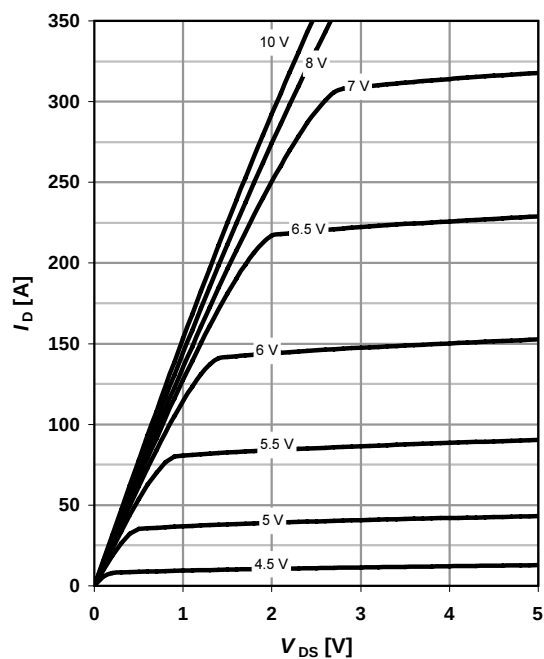
parameter:  $D = t_p/T$



### 5 Typ. output characteristics

$$I_D = f(V_{DS}); T_J = 25^\circ\text{C}$$

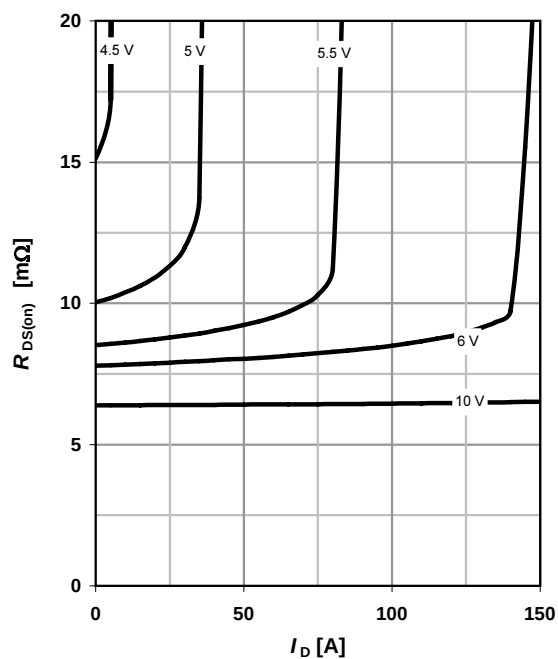
parameter:  $V_{GS}$



### 6 Typ. drain-source on resistance

$$R_{DS(on)} = f(I_D); T_J = 25^\circ\text{C}$$

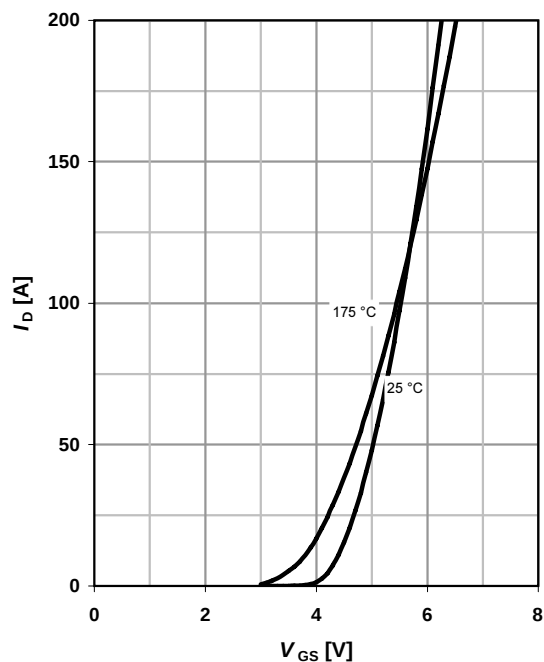
parameter:  $V_{GS}$



### 7 Typ. transfer characteristics

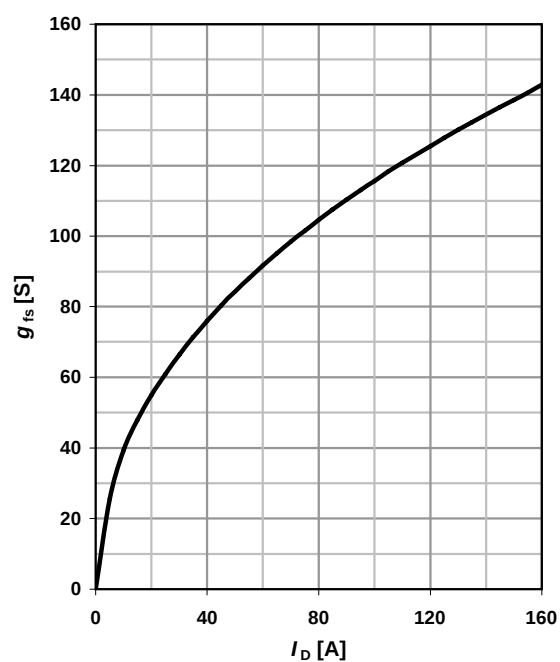
$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$

parameter:  $T_J$



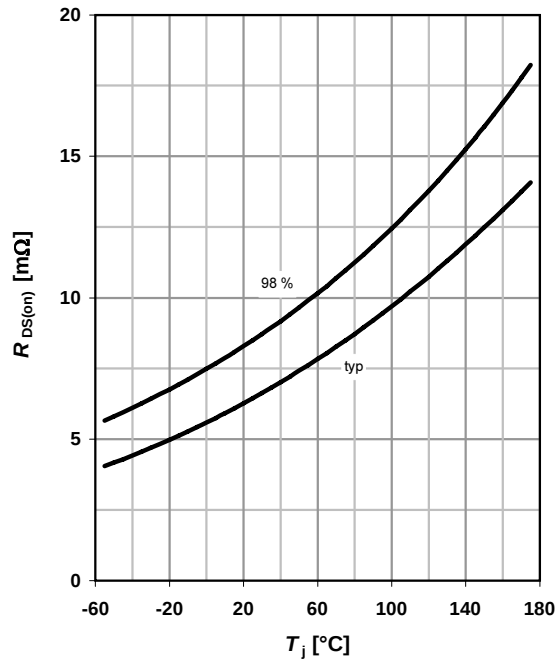
### 8 Typ. forward transconductance

$$g_{fs} = f(I_D); T_J = 25^\circ\text{C}$$



### 9 Drain-source on-state resistance

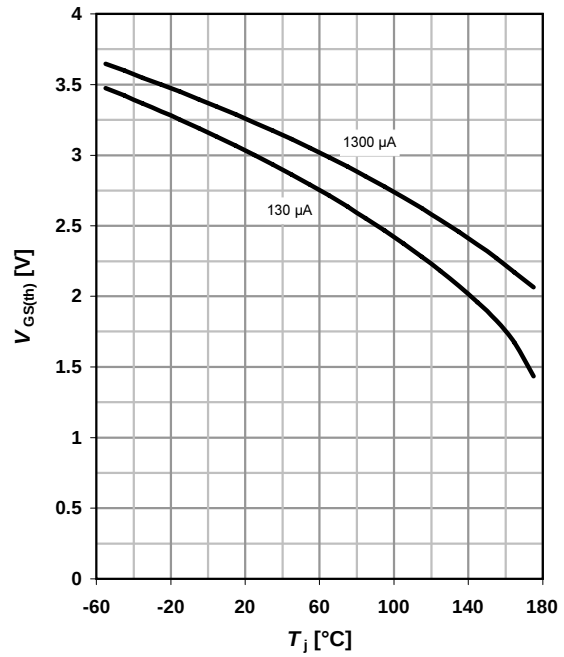
$$R_{DS(on)} = f(T_j); I_D = 95 \text{ A}; V_{GS} = 10 \text{ V}$$



### 10 Typ. gate threshold voltage

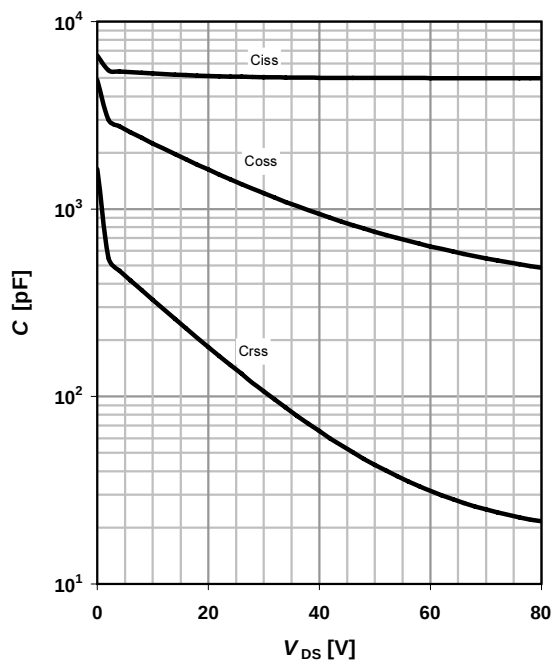
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter:  $I_D$



### 11 Typ. capacitances

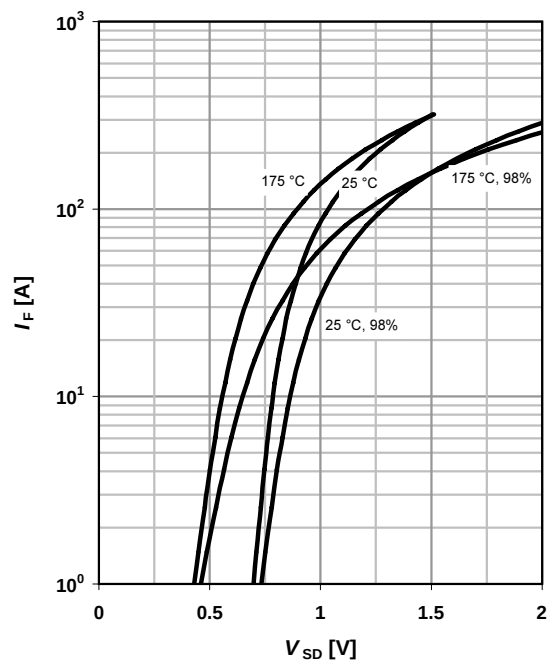
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$



### 12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

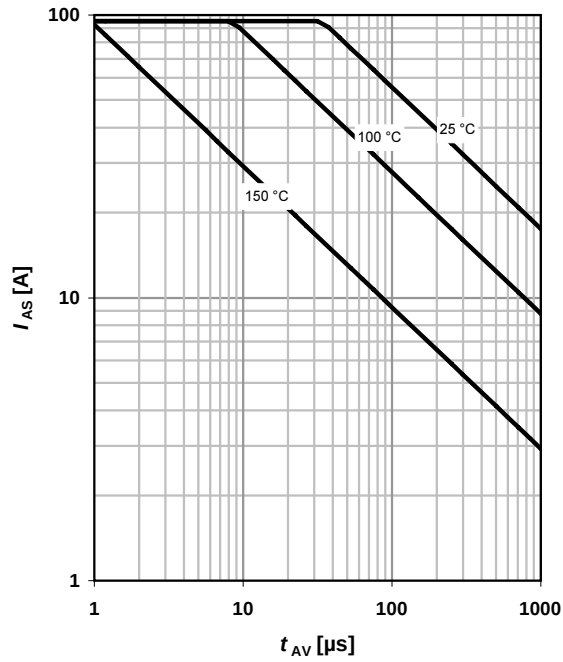
parameter:  $T_j$



### 13 Avalanche characteristics

$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega$$

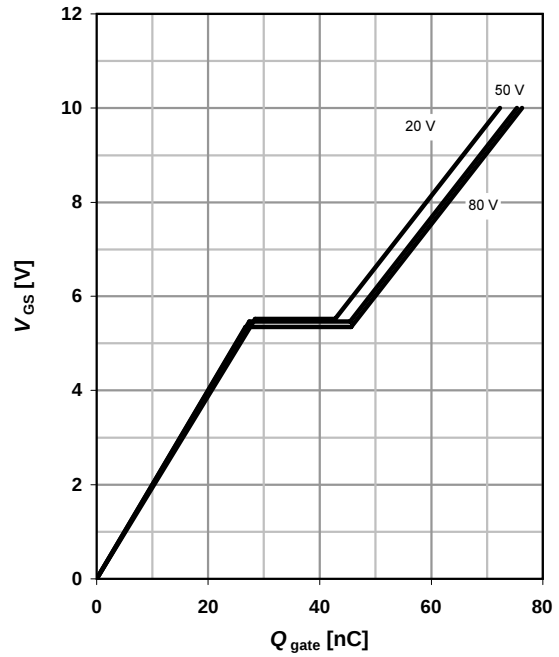
parameter:  $T_{j(\text{start})}$



### 14 Typ. gate charge

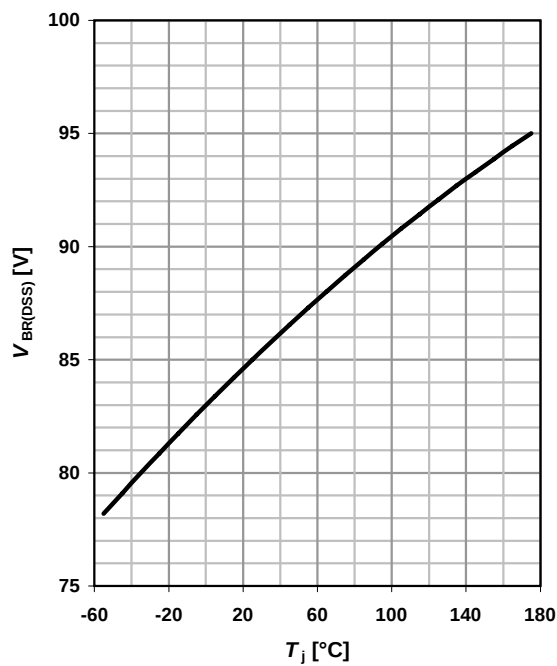
$$V_{GS}=f(Q_{\text{gate}}); I_D=95\ \text{A pulsed}$$

parameter:  $V_{DD}$

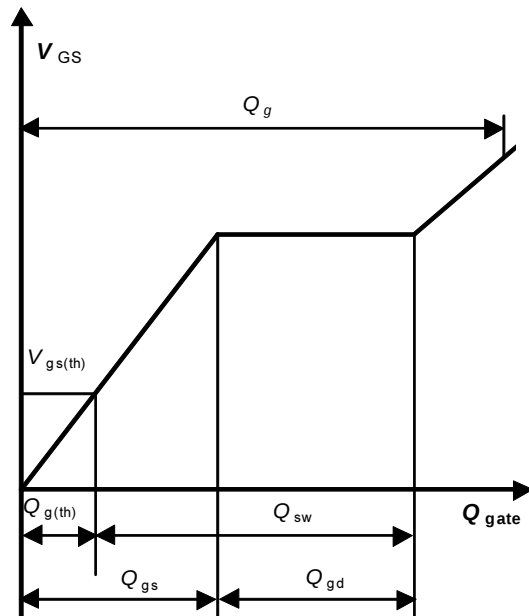


### 15 Drain-source breakdown voltage

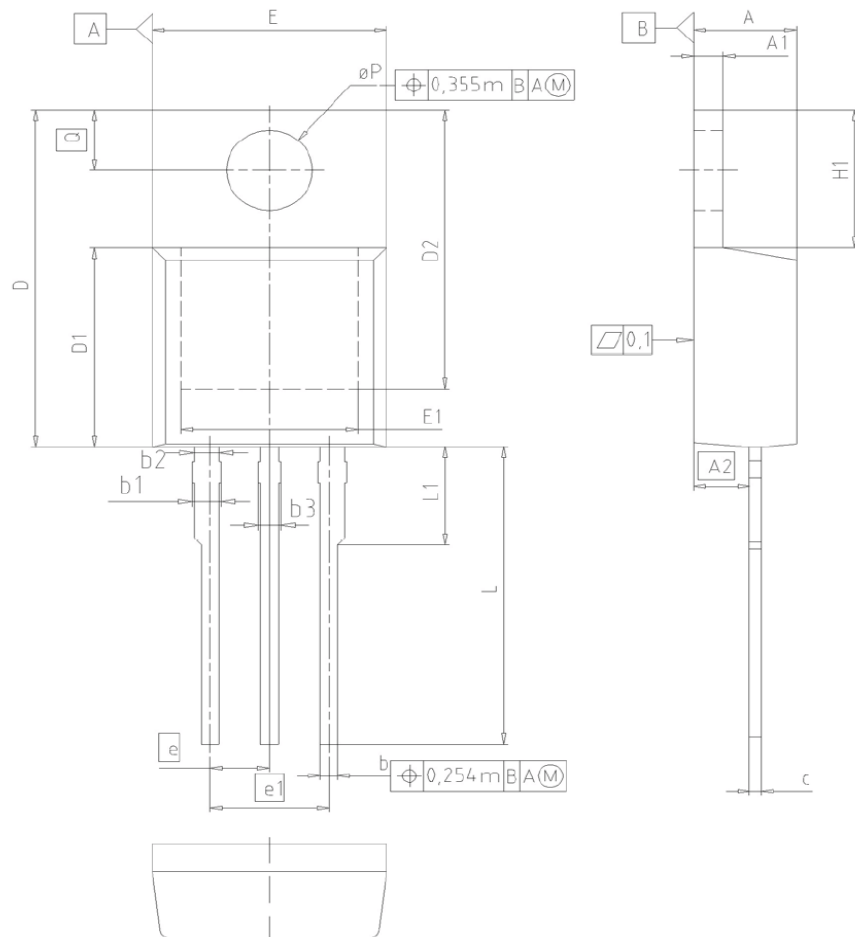
$$V_{BR(DSS)}=f(T_j); I_D=1\ \text{mA}$$



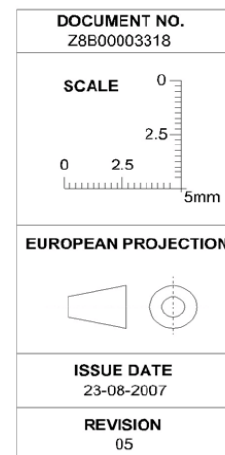
### 16 Gate charge waveforms

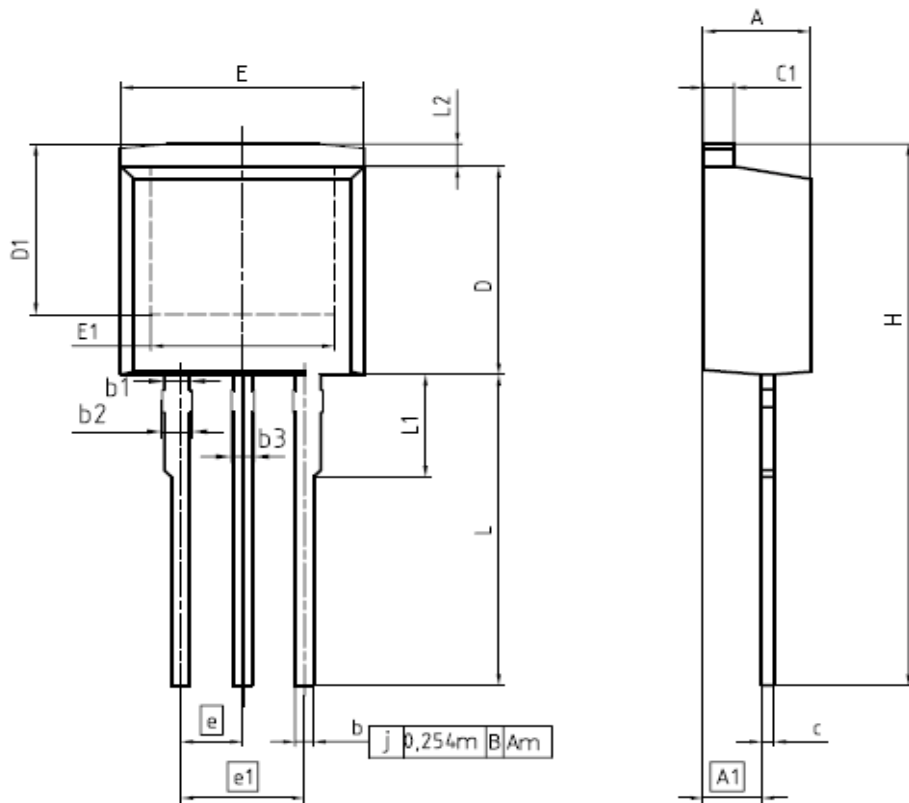


PG-TO220-3: Outline

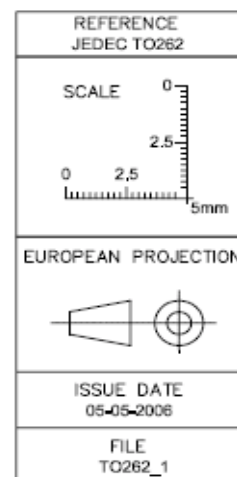


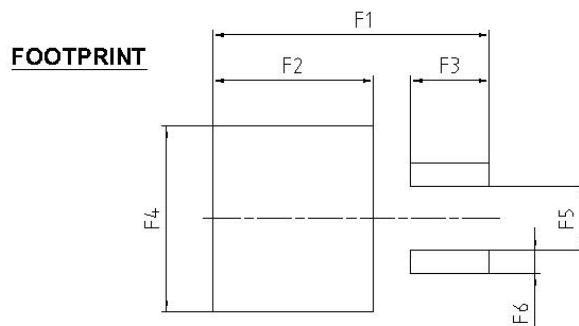
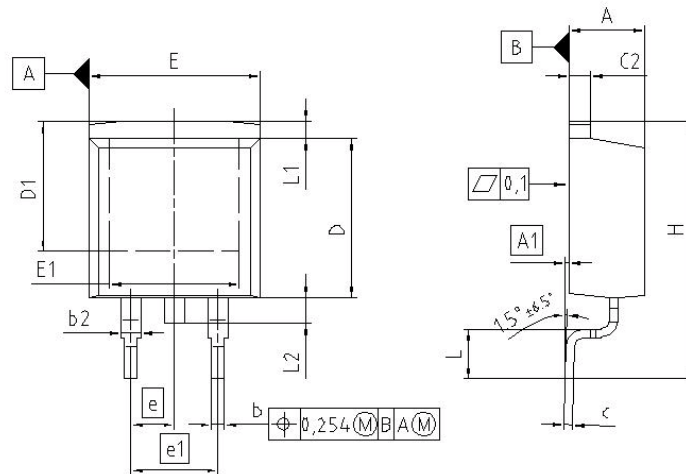
| DIM      | MILLIMETERS |       | INCHES |       |
|----------|-------------|-------|--------|-------|
|          | MIN         | MAX   | MIN    | MAX   |
| A        | 4.30        | 4.57  | 0.169  | 0.180 |
| A1       | 1.17        | 1.40  | 0.046  | 0.055 |
| A2       | 2.15        | 2.72  | 0.085  | 0.107 |
| b        | 0.65        | 0.86  | 0.026  | 0.034 |
| b1       | 0.95        | 1.40  | 0.037  | 0.055 |
| b2       | 0.95        | 1.15  | 0.037  | 0.045 |
| b3       | 0.65        | 1.15  | 0.026  | 0.045 |
| c        | 0.33        | 0.80  | 0.013  | 0.024 |
| D        | 14.81       | 15.95 | 0.583  | 0.628 |
| D1       | 8.51        | 9.45  | 0.335  | 0.372 |
| D2       | 12.19       | 13.10 | 0.480  | 0.516 |
| E        | 9.70        | 10.36 | 0.382  | 0.408 |
| E1       | 6.50        | 8.60  | 0.256  | 0.339 |
| e        | 2.54        |       | 0.100  |       |
| e1       | 5.08        |       | 0.200  |       |
| N        | 3           |       | 3      |       |
| H1       | 5.90        | 6.90  | 0.232  | 0.272 |
| L        | 13.00       | 14.00 | 0.512  | 0.551 |
| L1       | -           | 4.80  | -      | 0.189 |
| $\phi P$ | 3.60        | 3.89  | 0.142  | 0.153 |
| Q        | 2.60        | 3.00  | 0.102  | 0.118 |



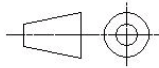
PG-TO262-3-1 (I<sup>2</sup>PAK)


| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 4,300       | 4,572  | 0,169  | 0,180 |
| A1  | 2,150       | 2,718  | 0,085  | 0,107 |
| b   | 0,650       | 0,864  | 0,026  | 0,034 |
| b1  | 0,950       | 1,093  | 0,037  | 0,043 |
| b2  | 0,950       | 1,400  | 0,037  | 0,055 |
| b3  | 0,650       | 1,118  | 0,026  | 0,044 |
| c   | 0,330       | 0,600  | 0,013  | 0,024 |
| c1  | 1,170       | 1,400  | 0,046  | 0,055 |
| D   | 8,509       | 9,450  | 0,335  | 0,372 |
| D1  | 6,900       | -      | 0,272  | -     |
| E   | 9,700       | 10,363 | 0,382  | 0,408 |
| E1  | 6,500       | 8,600  | 0,256  | 0,339 |
| e   | 2,540       |        | 0,100  |       |
| e1  | 5,080       |        | 0,200  |       |
| N   | 3           |        | 3      |       |
| L   | 13,000      | 14,000 | 0,512  | 0,551 |
| L1  | -           | 4,800  | -      | 0,189 |
| L2  | -           | 1,727  | -      | 0,068 |



PG-TO-263 (D<sup>2</sup>-Pak)


| DIM | MILLIMETERS |        | INCHES |       |
|-----|-------------|--------|--------|-------|
|     | MIN         | MAX    | MIN    | MAX   |
| A   | 4.300       | 4.572  | 0.169  | 0.180 |
| A1  | 0.000       | 0.254  | 0.000  | 0.010 |
| b   | 0.650       | 0.850  | 0.026  | 0.033 |
| b2  | 0.950       | 1.321  | 0.037  | 0.052 |
| c   | 0.330       | 0.650  | 0.013  | 0.026 |
| c2  | 0.170       | 1.400  | 0.046  | 0.055 |
| D   | 8.509       | 9.450  | 0.335  | 0.372 |
| D1  | 7.100       | -      | 0.280  | -     |
| E   | 9.800       | 10.312 | 0.386  | 0.406 |
| E1  | 6.500       | -      | 0.256  | -     |
| e   | 2.540       |        | 0.100  |       |
| e1  | 5.080       |        | 0.200  |       |
| N   | 2           |        | 2      |       |
| H   | 14.605      | 15.875 | 0.575  | 0.625 |
| L   | 2.200       | 3.000  | 0.087  | 0.118 |
| L1  | -           | 1.600  | -      | 0.063 |
| L2  | 1.000       | 1.778  | 0.039  | 0.070 |
| F1  | 16.050      | 16.250 | 0.632  | 0.640 |
| F2  | 9.300       | 9.500  | 0.366  | 0.374 |
| F3  | 4.500       | 4.700  | 0.177  | 0.185 |
| F4  | 10.700      | 10.900 | 0.421  | 0.429 |
| F5  | 3.630       | 3.830  | 0.143  | 0.151 |
| F6  | 1.100       | 1.300  | 0.043  | 0.051 |

|                                                                                                                     |
|---------------------------------------------------------------------------------------------------------------------|
| <b>REFERENCE</b><br>JEDEC TO263                                                                                     |
| <b>SCALE</b><br>0 5 5 7.5mm                                                                                         |
| <b>EUROPEAN PROJECTION</b><br> |
| <b>ISSUE DATE</b><br>12-02-2006                                                                                     |
| <b>FILE</b><br>TO263_2                                                                                              |

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